(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
23 September 2010 (23.09.2010)

PCT

(10) International Publication Number
WO 2010/105955 A1

(51) International Patent Classification:
H01L 21/302 (2006.01) *H01L 21/762* (2006.01)

(21) International Application Number:
PCT/EP2010/053050

(22) International Filing Date:
10 March 2010 (10.03.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0951690 17 March 2009 (17.03.2009) FR

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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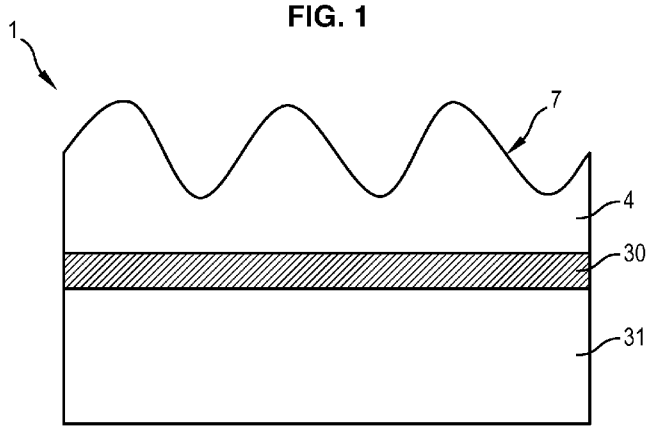
— *of inventorship (Rule 4.17(iv))*

Published:

— *with international search report (Art. 21(3))*

(54) **Title**: FINISHING METHOD FOR MANUFACTURING SUBSTRATES IN THE FIELD OF ELECTRONICS

FIG. 1



(57) **Abstract**: The invention relates to a method for finishing the surface of semiconducting substrate (1), said substrate comprising a set of layers comprising a useful semiconducting layer (4) on at least one of the faces of said substrate (1), said useful layer (4) comprising a rough free surface (7), said method being suitable for smoothing out the free surface (7), said method being characterized in that it comprises the successive steps of : - creating a protective layer (20) covering the surface (7) of the useful layer (4) with a thickness 1 to 3 times larger than the peak-to-valley distance of said surface (7) of the useful layer (4), - at least one polishing-oxidation sequence, said sequence comprising the successive steps of : polishing the surface (21) of the protective layer (20), said polishing being adjusted so as not to attack the useful layer (4), and performing a thermal oxidation with supply of oxygen gas of the substrate (1), in order to transform a portion of the useful layer (4) into an oxide layer (16), in order to reduce the roughness of the surface (7) of the useful layer (4).

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